

74AHC2G125; 74AHCT2G125

Dual buffer/line driver; 3-state

Rev. 02 — 22 December 2008

Product data sheet

1. General description

The 74AHC2G125 and 74AHCT2G125 are high-speed Si-gate CMOS devices. They provide a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{nOE}). A HIGH at \overline{nOE} causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - ◆ MM JESD22-A115-A: exceeds 200 V
 - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AHC2G125DP 74AHCT2G125DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHC2G125DC 74AHCT2G125DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AHC2G125GD 74AHCT2G125GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2

4. Marking

Table 2. Marking codes

Type number	Marking
74AHC2G125DP	A25
74AHCT2G125DP	C25
74AHC2G125DC	A25
74AHCT2G125DC	C25
74AHC2G125GD	A25
74AHCT2G125GD	C25

5. Functional diagram

Fig 1. Logic symbol

Fig 2. IEC logic symbol

Fig 3. Logic diagram (one buffer)

6. Pinning information

6.1 Pinning

Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

Fig 5. Pin configuration SOT996-2 (XSON8U)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1 \overline{OE} , 2 \overline{OE}	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Control	Input	Output
n \overline{OE}	nA	nY
L	L	L
L	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
V _I	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	[1] -20	-	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	[1] -	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
 For XSON8U package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G125			74AHCT2G125			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V _I	input voltage		0	-	5.5	0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V _{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G125										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = -50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
I _O = -8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V		
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V		
I _{OZ}	OFF-state output current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	μA
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	μA

Table 7. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _I	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT2G125										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	0.25	-	2.5	-	10	µA
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA
ΔI _{CC}	additional supply current	per input pin; V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics
 GND = 0 V; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G125										
t _{pd}	propagation delay	nA to nY; see Figure 6								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	4.7	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF	-	6.6	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF	-	4.8	7.5	1.0	8.5	1.0	9.5	ns

Table 8. Dynamic characteristics ...continued
GND = 0 V; for test circuit see [Figure 8](#).

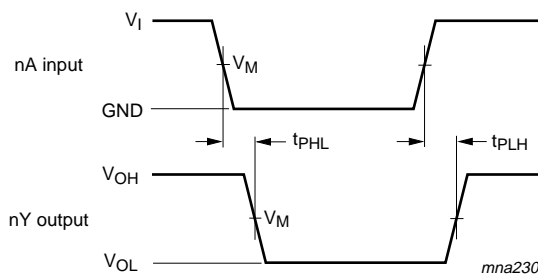
Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{en}	enable time	n $\overline{O}E$ to nY; see Figure 7 [1]								
		V _{CC} = 3.0 V to 3.6 V [2]								
		C _L = 15 pF	-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		C _L = 50 pF	-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		C _L = 50 pF	-	4.9	7.5	1.0	8.5	1.0	9.5	ns
t _{dis}	disable time	n $\overline{O}E$ to nY; see Figure 7 [1]								
		V _{CC} = 3.0 V to 3.6 V [2]								
		C _L = 15 pF	-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		C _L = 50 pF	-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF	-	5.7	8.8	1.0	10.0	1.0	11.0	ns
C _{PD}	power dissipation capacitance	per buffer; C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC} [4]	-	9	-	-	-	-	-	pF
74AHCT2G125										
t _{pd}	propagation delay	nA to nY; see Figure 6 [1]								
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	3.4	5.5	1.0	6.5	1.0	6.5	ns
		C _L = 50 pF	-	4.8	7.5	1.0	8.5	1.0	8.5	ns
t _{en}	enable time	n $\overline{O}E$ to nY; see Figure 7 [1]								
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	3.9	5.1	1.0	6.0	1.0	6.0	ns
		C _L = 50 pF	-	5.1	7.5	1.0	8.5	1.0	8.5	ns
t _{dis}	disable time	n $\overline{O}E$ to nY; see Figure 7 [1]								
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	4.5	6.8	1.0	8.0	1.0	8.0	ns
		C _L = 50 pF	-	6.1	8.8	1.0	10.0	1.0	10.0	ns

Table 8. Dynamic characteristics ...continued
GND = 0 V; for test circuit see Figure 8.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _{PD}	power dissipation capacitance	per buffer; C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	[4] -	11	-	-	-	-	-	pF

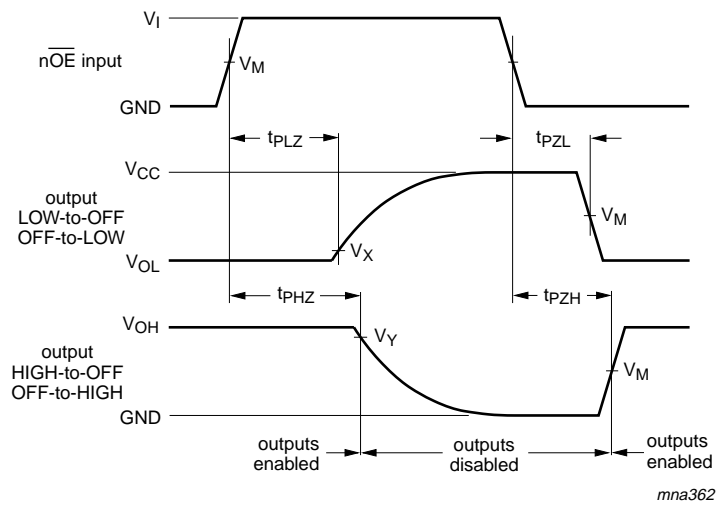
- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
 t_{en} is the same as t_{PZL} and t_{PZH}.
 t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- [2] Typical values are measured at V_{CC} = 3.3 V.
- [3] Typical values are measured at V_{CC} = 5.0 V.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in Volts.

12. Waveforms



Measurement points are given in [Table 9](#).
 Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Input (nA) to output (nY) propagation delays



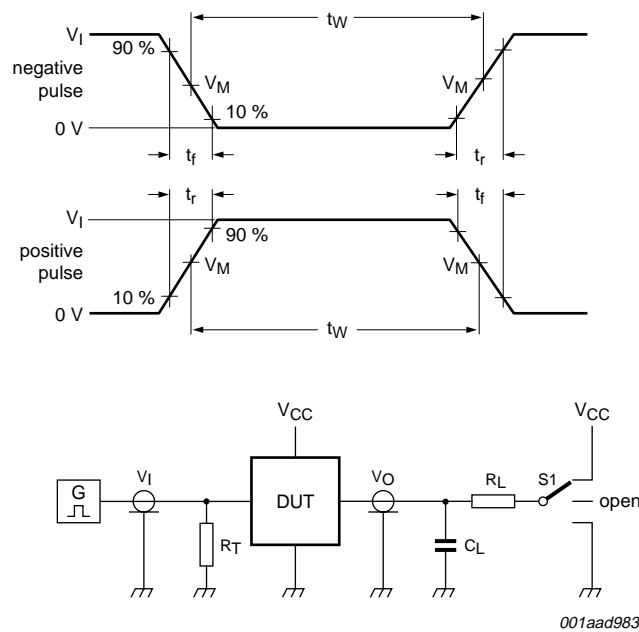
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. Enable and disable times

Table 9. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC2G125	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
74AHCT2G125	1.5 V	$0.5V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$



Test data is given in [Table 10](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC2G125	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74AHCT2G125	3 V	≤ 3 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

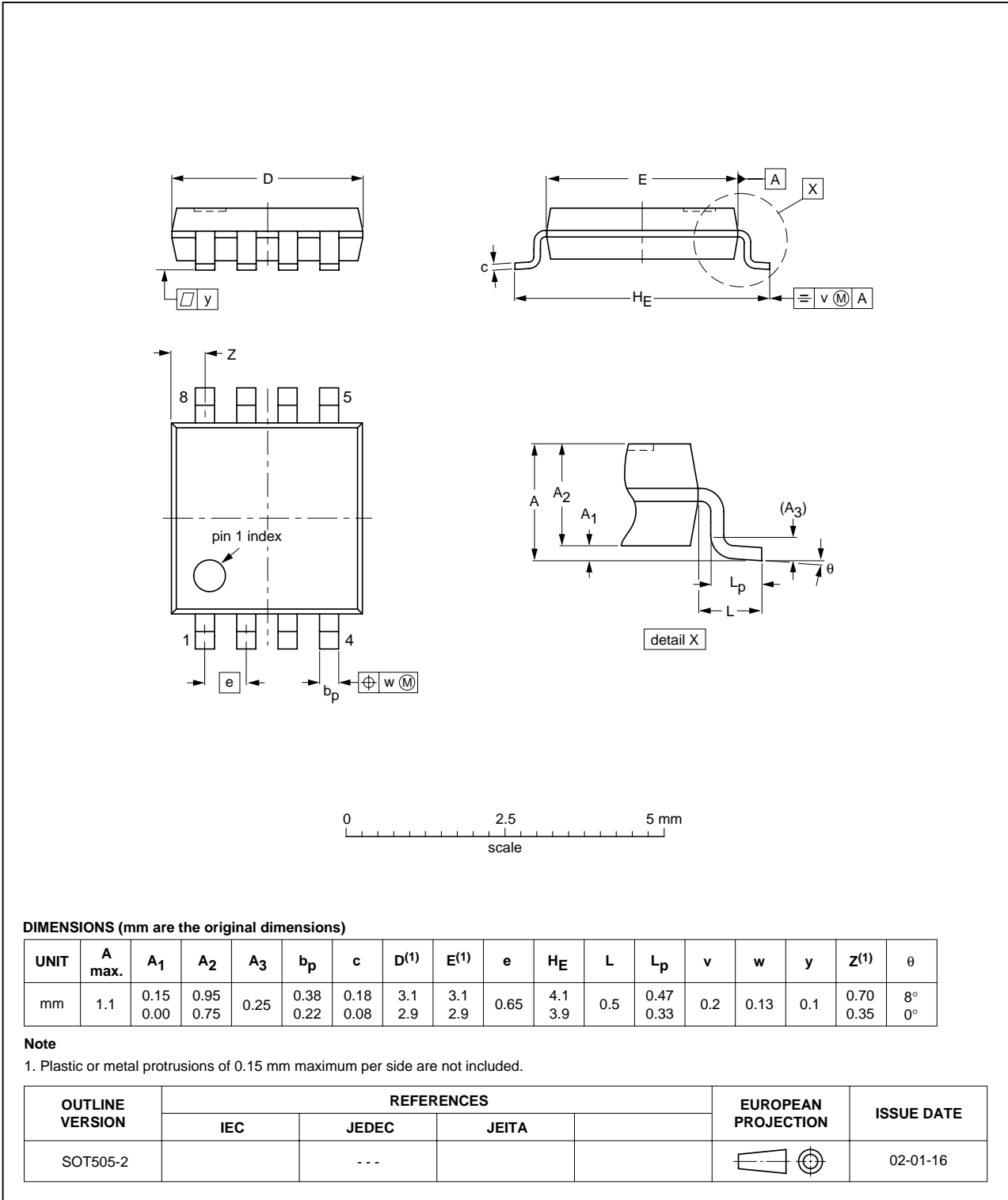


Fig 9. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

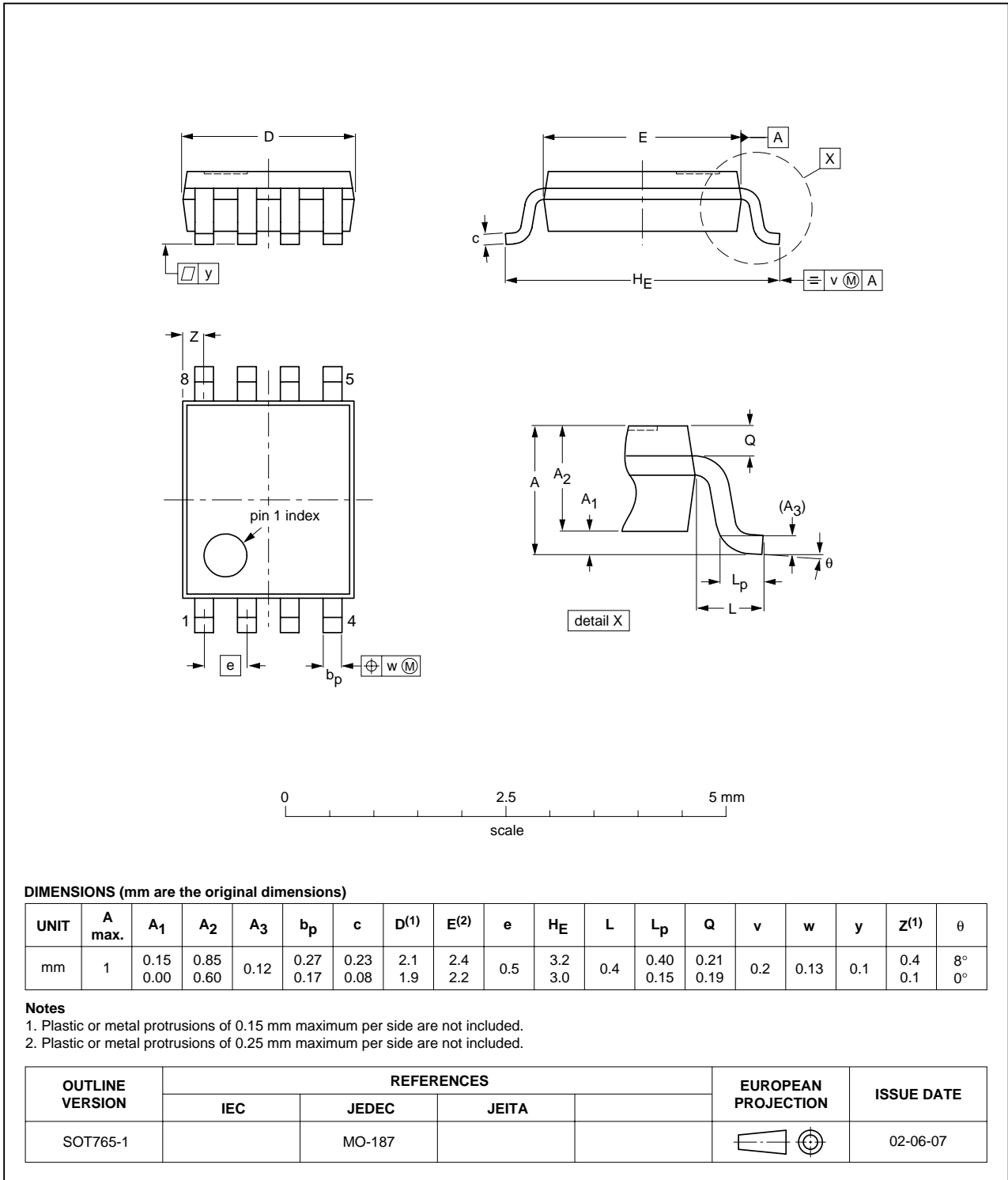


Fig 10. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

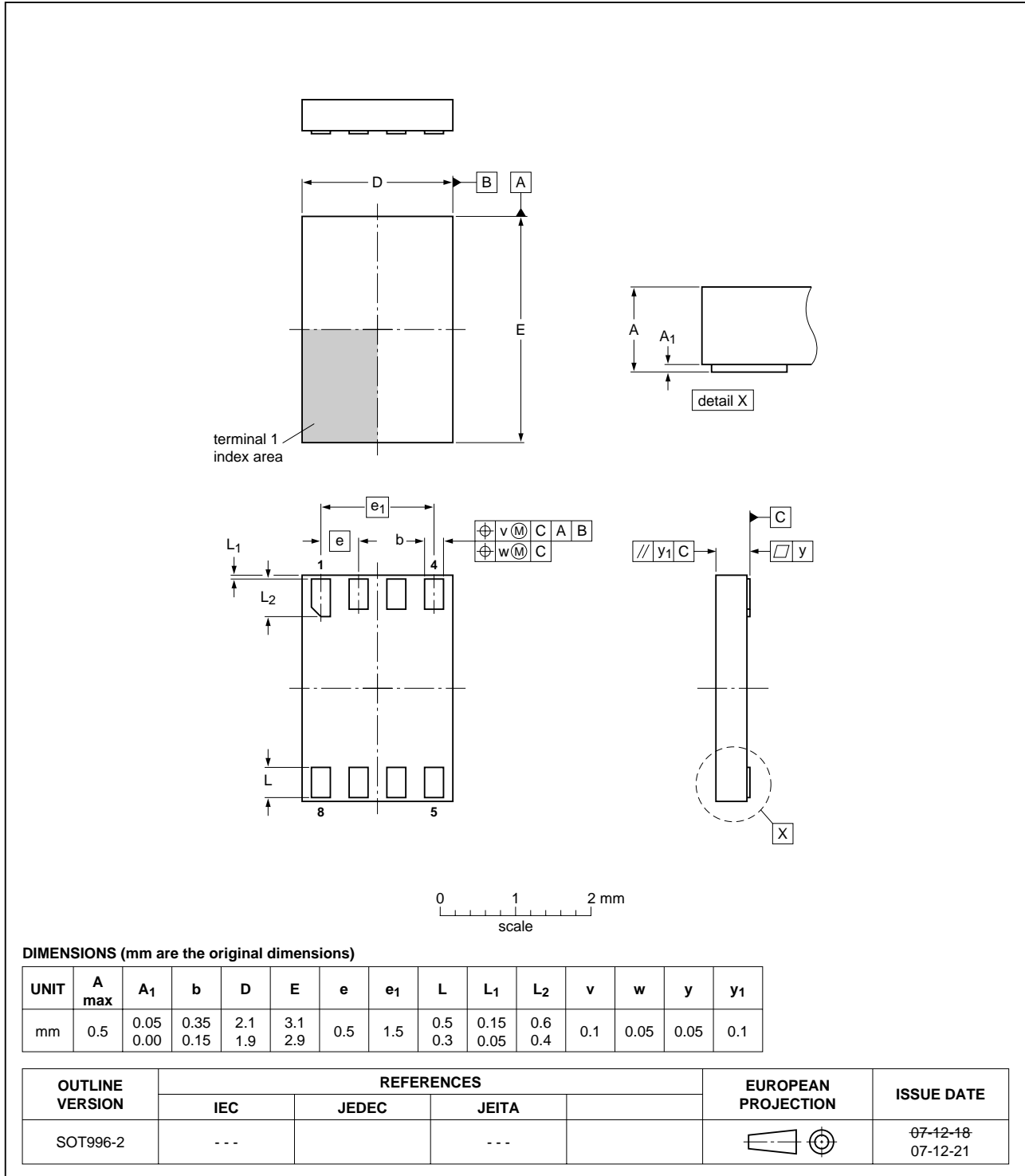


Fig 11. Package outline SOT996-2 (XSON8U)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G125_2	20081222	Product data sheet	-	74AHC_AHCT2G125_1
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Added type number 74AHC2G125GD and 74AHCT2G125GD (XSON8U package). 			
74AHC_AHCT2G125_1	20040113	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 22 December 2008

Document identifier: 74AHC_AHCT2G125_2